Low-Voltage 1.8/2.5/3.3V 16-Bit Transparent Latch

With 3.6V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The NL74VCXH16373 is an advanced performance, non–inverting 16–bit transparent latch. It is designed for very high–speed, very low–power operation in 1.8V, 2.5V or 3.3V systems. The VCX16373 is byte controlled, with each byte functioning identically, but independently. Each byte has separate Output Enable and Latch Enable inputs. These control pins can be tied together for full 16–bit operation.

When operating at 2.5V (or 1.8V) the part is designed to tolerate voltages it may encounter on either inputs or outputs when interfacing to 3.3V busses. It is guaranteed to be over–voltage tolerant to 3.6V.

The NL74VCXH16373 contains 16 D-type latches with 3-state 3.6V-tolerant outputs. When the Latch Enable (LEn) inputs are HIGH, data on the Dn inputs enters the latches. In this condition, the latches are transparent, (a latch output will change state each time its D input changes). When LE is LOW, the latch stores the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The 3-state outputs are controlled by the Output Enable ($\overline{\text{OEn}}$) inputs. When $\overline{\text{OE}}$ is LOW, the outputs are enabled. When $\overline{\text{OE}}$ is HIGH, the standard outputs are in the high impedance state, but this does not interfere with new data entering into the latches. The data inputs include active bushold circuitry, eliminating the need for external pull-up resistors to hold unused or floating inputs at a valid logic state.

- Designed for Low Voltage Operation: VCC = 1.65-3.6V
- 3.6V Tolerant Inputs and Outputs
- High Speed Operation: 3.0ns max for 3.0 to 3.6V

3.9ns max for 2.3 to 2.7V 6.8ns max for 1.65 to 1.95V

• Static Drive: ±24mA Drive at 3.0V

±18mA Drive at 2.3V ±6mA Drive at 1.65V

- Supports Live Insertion and Withdrawal
- Includes Active Bushold to Hold Unused or Floating Inputs at a Valid Logic State
- IOFF Specification Guarantees High Impedance When $V_{CC} = 0V^{\dagger}$
- Near Zero Static Supply Current in All Three Logic States (20μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds ±300mA @ 125°C
- ESD Performance: Human Body Model >2000V; Machine Model >200V

†NOTE: To ensure the outputs activate in the 3–state condition, the output enable pins should be connected to V_{CC} through a pull–up resistor. The value of the resistor is determined by the current sinking capability of the output connected to the \overline{OE} pin.



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TSSOP-48 DT SUFFIX CASE 1201

MARKING DIAGRAM

8

NL74VCXH16373DT

AWLYYWW

O

1

A = Assembly Location

WL = Wafer Lot

YY = Year

WW = Work Week

PIN NAMES

Pins	Function
OEn	Output Enable Inputs
LEn	Latch Enable Inputs
D0-D15	Inputs
O0-O15	Outputs

ORDERING INFORMATION

Device	Package	Shipping
NL74VCXH16373DT	TSSOP	39 / Rail
NL74VCXH16373DTR	TSSOP	2500 / Reel

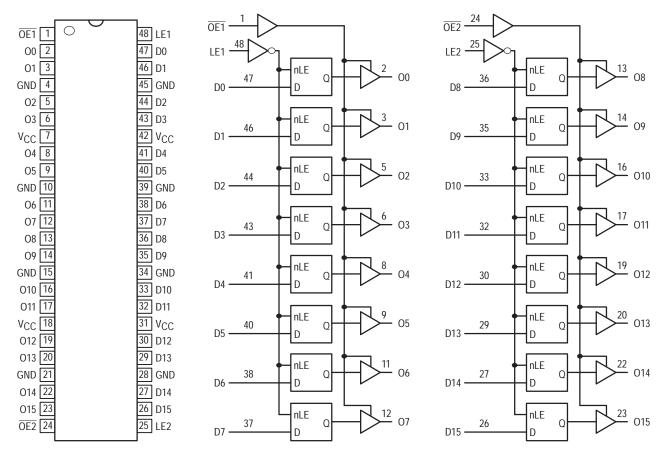
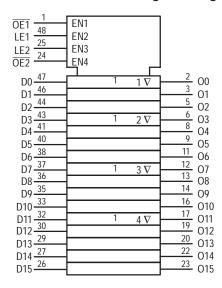


Figure 1. 48-Lead Pinout (Top View)

Figure 2. Logic Diagram



	Inputs		Outputs		Inputs		Outputs
LE1	OE1	D0:7	O0:7	LE2	OE2	D8:15	O8:15
Х	Н	Х	Z	Х	Н	Х	Z
Н	L	L	L	Н	L	L	L
Н	L	Н	Н	Н	L	Н	Н
L	L	Х	O0	L	L	Х	00

H = High Voltage Level; L = Low Voltage Level; Z = High Impedance State; X = High or Low Voltage Level and Transitions Are Acceptable, for I_{CC} reasons, DO NOT FLOAT Inputs. O0 = No Change.

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +4.6$		V
VO	DC Output Voltage	$-0.5 \le V_{O} \le +4.6$	Output in 3–State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1.; Outputs Active	V
ΙΙΚ	DC Input Diode Current	-50	V _I < GND	mA
lok	DC Output Diode Current	-50	V _O < GND	mA
		+50	AO > ACC	mA
IO	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
VCC	Supply Voltage	Operating Data Retention Only	1.65 1.2	3.3 3.3	3.6 3.6	V
VI	Input Voltage		-0.3		3.6	V
VO	Output Voltage	(Active State) (3–State)	0 0		V _C C 3.6	V
IOH	HIGH Level Output Current, V _{CC} = 3.0V – 3.6V				-24	mA
lOL	LOW Level Output Current, V _{CC} = 3.0V – 3.6V				24	mA
lOH	HIGH Level Output Current, V _{CC} = 2.3V – 2.7V				-18	mA
lOL	LOW Level Output Current, V _{CC} = 2.3V – 2.7V				18	mA
loh	HIGH Level Output Current, V _{CC} = 1.65 – 1.95V				-6	mA
l _{OL}	LOW Level Output Current, V _{CC} = 1.65 – 1.95V				6	mA
TA	Operating Free–Air Temperature		-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8V to	2.0V, V _{CC} = 3.0V	0		10	ns/V

^{1.} IO absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°		
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2.)	1.65V ≤ V _{CC} < 2.3V	0.65 x V _C C		V
		2.3V ≤ V _{CC} ≤ 2.7V	1.6		
		2.7V < V _{CC} ≤ 3.6V	2.0		
VIL	LOW Level Input Voltage (Note 2.)	1.65V ≤ V _{CC} < 2.3V		0.35 x V _{CC}	V
		2.3V ≤ V _{CC} ≤ 2.7V		0.7	
		2.7V < V _{CC} ≤ 3.6V		0.8	
Vон	HIGH Level Output Voltage	1.65V ≤ V _{CC} ≤ 3.6 V; I _{OH} = -100 μA	V _{CC} - 0.2		V
		V _{CC} = 1.65V; I _{OH} = -6mA	1.25		
		V _{CC} = 2.3V; I _{OH} = -6mA	2.0		
		V _{CC} = 2.3V; I _{OH} = -12mA	1.8		
		V _{CC} = 2.3V; I _{OH} = -18mA	1.7		
		V _{CC} = 2.7V; I _{OH} = -12mA	2.2		
		V _{CC} = 3.0V; I _{OH} = -18mA	2.4		
		V _{CC} = 3.0V; I _{OH} = -24mA	2.2		
VOL	LOW Level Output Voltage	$1.65V \le V_{CC} \le 3.6V$; $I_{OL} = 100\mu A$		0.2	V
		V _{CC} = 1.65V; I _{OL} = 6mA		0.3	
		V _{CC} = 2.3V; I _{OL} = 12mA		0.4	
		V _{CC} = 2.3V; I _{OL} = 18mA		0.6	
		V _{CC} = 2.7V; I _{OL} = 12mA		0.4	
		V _{CC} = 3.0V; I _{OL} = 18mA		0.4	
		V _{CC} = 3.0V; I _{OL} = 24mA		0.55	
lı	Input Leakage Current	$1.65V \le V_{CC} \le 3.6V; \ 0V \le V_{I} \le 3.6V$		±5.0	μΑ
I _I (HOLD)	Minimum Bushold Input Current	$V_{CC} = 3.0V, V_{IN} = 0.8V$	75		μΑ
		V _{CC} = 3.0V, V _{IN} = 2.0V	-75		
		V _{CC} = 2.3V, V _{IN} = 0.7V	45		
		V _{CC} = 2.3V, V _{IN} = 1.6V	-45		
		V _{CC} = 1.65V, V _{IN} = 0.57V	25		
		V _{CC} = 1.65V, V _{IN} = 1.07V	-25		
I _I (OD)	Minimum Bushold Over-Drive	V _{CC} = 3.6V, (Note 3.)	450		μΑ
, ,	Current Needed to Change State	V _{CC} = 3.6V, (Note 4.)	-450		
		V _{CC} = 2.7V, (Note 3.)	300		
		V _{CC} = 2.7V, (Note 4.)	-300		
		V _{CC} = 1.95V, (Note 3.)	200		
		V _{CC} = 1.95V, (Note 4.)	-200		
loz	3–State Output Current	$1.65V \le V_{CC} \le 3.6V; \ 0V \le V_O \le 3.6V;$ $V_I = V_{IH} \text{ or } V_{IL}$		±10	μА
lOFF	Power-Off Leakage Current	$V_{CC} = 0V$; V_I or $V_O = 3.6V$		10	μΑ
ICC	Quiescent Supply Current (Note 5.)	1.65V ≤ V _{CC} ≤ 3.6V; V _I = GND or V _{CC}		20	μΑ
		1.65V ≤ V _{CC} ≤ 3.6V; 3.6V ≤ V _I , V _O ≤ 3.6V		±20	μΑ
Δl _{CC}	Increase in I _{CC} per Input	2.7V < V _{CC} ≤ 3.6V; V _{IH} = V _{CC} − 0.6V		750	μА

^{2.} These values of V_I are used to test DC electrical characteristics only.

3. An external driver must source at least the specified current to switch from LOW–to–HIGH

4. An external driver must source at least the specified current to switch from HIGH–to–LOW

5. Outputs disabled or 3–state only.

AC CHARACTERISTICS (Note 6.; $t_R = t_F = 2.0$ ns; $C_L = 30$ pF; $R_L = 500\Omega$)

			Limits						
				T _A = -40°C to +85°C					
			V _{CC} = 3.0	V to 3.6V	V _{CC} = 2.3	8V to 2.7V	V _{CC} = 1.6	5 to 1.95V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
^t PLH ^t PHL	Propagation Delay Dn to On	1	0.8 0.8	3.0 3.0	1.0 1.0	3.4 3.4	1.5 1.5	6.8 6.8	ns
^t PLH ^t PHL	Propagation Delay LE to On	1	0.8 0.8	3.0 3.0	1.0 1.0	3.9 3.9	1.5 1.5	7.8 7.8	ns
tPZH tPZL	Output Enable Time to High and Low Level	2	0.8 0.8	3.5 3.5	1.0 1.0	4.6 4.6	1.5 1.5	9.2 9.2	ns
tPHZ tPLZ	Output Disable Time From High and Low Level	2	0.8 0.8	3.5 3.5	1.0 1.0	3.8 3.8	1.5 1.5	6.8 6.8	ns
t _S	Setup Time, High or Low Dn to LE	3	1.5		1.5		2.5		ns
th	Hold Time, High or Low Dn to LE	3	1.0		1.0		1.0		ns
t _W	LE Pulse Width, High	3	1.5		1.5		4.0		ns
^t OSHL ^t OSLH	Output-to-Output Skew (Note 7.)			0.5 0.5		0.5 0.5		0.75 0.75	ns

^{6.} For $C_L = 50 pF$, add approximately 300ps to the AC maximum specification.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C	
Symbol	Characteristic	Condition	Тур	Unit
VOLP	Dynamic LOW Peak Voltage	$V_{CC} = 1.8V$, $C_L = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	0.25	V
	(Note 8.)	$V_{CC} = 2.5V$, $C_{L} = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	0.6]
		$V_{CC} = 3.3V$, $C_L = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	0.8]
VOLV	Dynamic LOW Valley Voltage	$V_{CC} = 1.8V$, $C_L = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	-0.25	V
	(Note 8.)	$V_{CC} = 2.5V$, $C_L = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	-0.6]
		$V_{CC} = 3.3V$, $C_L = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	-0.8	
VOHV	Dynamic HIGH Valley Voltage	$V_{CC} = 1.8V$, $C_L = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	1.5	V
	(Note 9.)	$V_{CC} = 2.5V$, $C_L = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	1.9]
		$V_{CC} = 3.3V$, $C_L = 30pF$, $V_{IH} = V_{CC}$, $V_{IL} = 0V$	2.2	

^{8.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

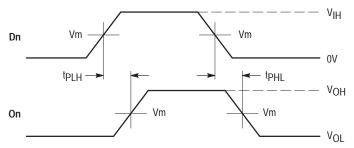
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	Note 10.	6	pF
COUT	Output Capacitance	Note 10.	7	pF
C _{PD}	Power Dissipation Capacitance	Note 10., 10MHz	20	pF

10. V_{CC} = 1.8, 2.5 or 3.3V; V_{I} = 0V or V_{CC} .

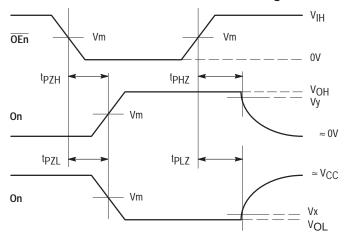
Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH—to—LOW (toshl) or LOW—to—HIGH (tosl); parameter guaranteed by design.

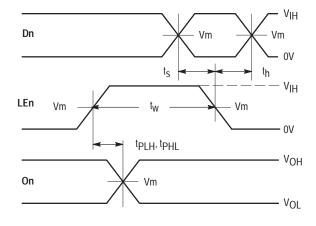
^{9.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the HIGH state.



WAVEFORM 1 – PROPAGATION DELAYS $t_R = t_F = 2.0 \text{ns}, 10\%$ to 90%; $f = 1 \text{MHz}; t_W = 500 \text{ns}$

Figure 3. AC Waveforms





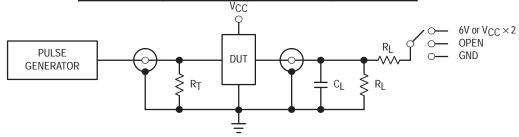
WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.0ns$, 10% to 90%; f = 1MHz; $t_W = 500ns$

WAVEFORM 3 – LE to On PROPAGATION DELAYS, LE MINIMUM PULSE WIDTH, Dn to LE SETUP AND HOLD TIMES

 $t_R = t_F = 2.0$ ns, 10% to 90%; f = 1MHz; $t_W = 500$ ns except when noted

Figure 4. AC Waveforms

	VCC			
Symbol	3.3V ±0.3V	2.5V ±0.2V	1.8V ±0.15V	
VIH	2.7V	Vcc	Vcc	
V _m	1.5V	V _{CC} /2	V _{CC} /2	
V _X	V _{OL} + 0.3V	V _{OL} + 0.15V	V _{OL} + 0.15V	
V _y	V _{OH} – 0.3V	V _{OH} – 0.15V	V _{OH} – 0.15V	



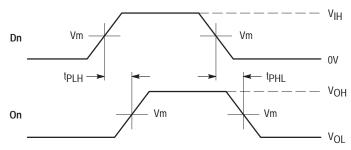
TEST	SWITCH
t _{PLH} , t _{PHL}	Open
tPZL, tPLZ	6V at $V_{CC} = 3.3 \pm 0.3V$; $V_{CC} \times 2$ at $V_{CC} = 2.5 \pm 0.2V$; 1.8V $\pm 0.15V$
t _{PZH} , t _{PHZ}	GND

C_L = 30pF or equivalent (Includes jig and probe capacitance)

 $R_{L} = 500\Omega$ or equivalent

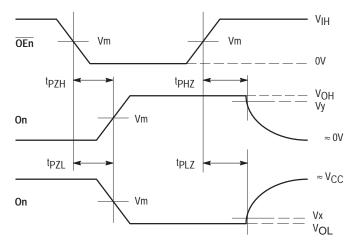
 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

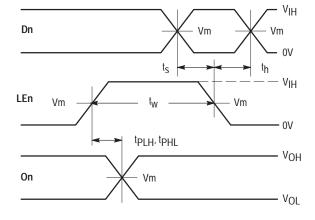
Figure 5. Test Circuit



WAVEFORM 4 – PROPAGATION DELAYS $t_R = t_F = 2.0 ns, 10\%$ to 90%; $f = 1 MHz; t_W = 500 ns$

Figure 6. AC Waveforms





WAVEFORM 5 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.0 \text{ns}$, 10% to 90%; f = 1 MHz; $t_W = 500 \text{ns}$

WAVEFORM 6 – LE to On PROPAGATION DELAYS, LE MINIMUM PULSE WIDTH, Dn to LE SETUP AND HOLD TIMES

 $t_R = t_F = 2.0$ ns, 10% to 90%; f = 1MHz; $t_W = 500$ ns except when noted

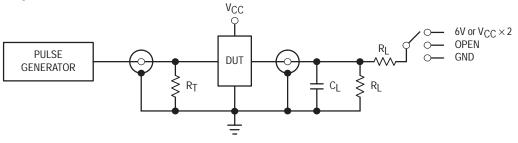
Figure 7. AC Waveforms

	Vcc		
Symbol	3.3V ±0.3V	2.7V	
VIH	2.7V	2.7V	
V _m	1.5V	1.5V	
V _X	V _{OL} + 0.3V	V _{OL} + 0.3V	
V _y	V _{OH} – 0.3V	V _{OH} – 0.3V	

AC CHARACTERISTICS ($t_R = t_F = 2.0ns$; $C_L = 50pF$; $R_L = 500\Omega$)

			Limits				
			T _A = -40°C to +85°C			1	
			V _{CC} = 3.0V to 3.6V V _{CC} = 2.7V			1	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit
^t PLH ^t PHL	Propagation Delay Dn to On	4	1.0 1.0	3.6 3.6		4.3 4.3	ns
^t PLH ^t PHL	Propagation Delay LE to On	4	1.0 1.0	3.9 3.9		4.6 4.6	ns
^t PZH ^t PZL	Output Enable Time to High and Low Level	5	1.0 1.0	4.7 4.7		5.7 5.7	ns
^t PHZ ^t PLZ	Output Disable Time From High and Low Level	5	1.0 1.0	4.1 4.1		4.5 4.5	ns
^t OSHL ^t OSLH	Output–to–Output Skew (Note 11.)			0.5 0.5		0.5 0.5	ns

^{11.} Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW(toSHL) or LOW-to-HIGH(toSLH); parameter guaranteed by design.

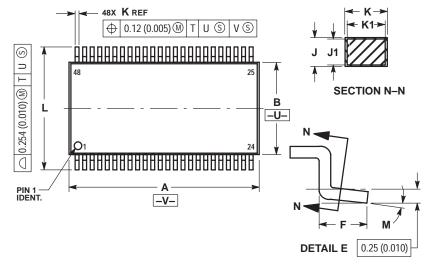


TEST	SWITCH
tPLH, tPHL	Open
tPZL, tPLZ	6V at $V_{CC} = 3.3 \pm 0.3V$; $V_{CC} \times 2$ at $V_{CC} = 2.5 \pm 0.2V$; 1.8V $\pm 0.15V$
tPZH, tPHZ	GND

 C_L = 50pF or equivalent (Includes jig and probe capacitance) R_L = 500 Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω) Figure 8. Test Circuit

PACKAGE DIMENSIONS

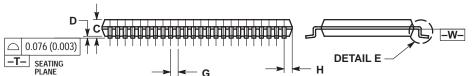
TSSOP DT SUFFIX CASE 1201-01 ISSUE A

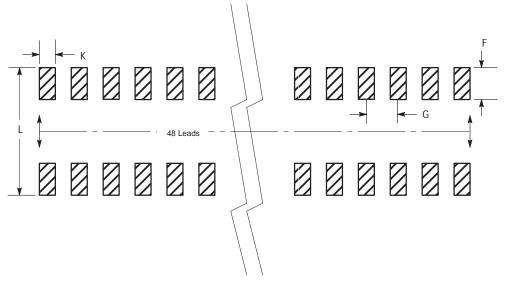


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS.
- SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION K DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 DIMENSIONS A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

DETERMINED AT DATOM FEARL -W							
	MILLIN	IETERS	INCHES				
DIM	MIN	MAX	MIN	MAX			
Α	12.40	12.60	0.488	0.496			
В	6.00	6.20	0.236	0.244			
С		1.10		0.043			
D	0.05	0.15	0.002	0.006			
F	0.50	0.75	0.020	0.030			
G	0.50	BSC	0.0197 BSC				
Н	0.37		0.015				
J	0.09	0.20	0.004	0.008			
J1	0.09	0.16	0.004	0.006			
K	0.17	0.27	0.007	0.011			
K1	0.17	0.23	0.007	0.009			
L	7.95	8.25	0.313	0.325			
M	0 °	8 °	0 °	8 °			





Package Footprint

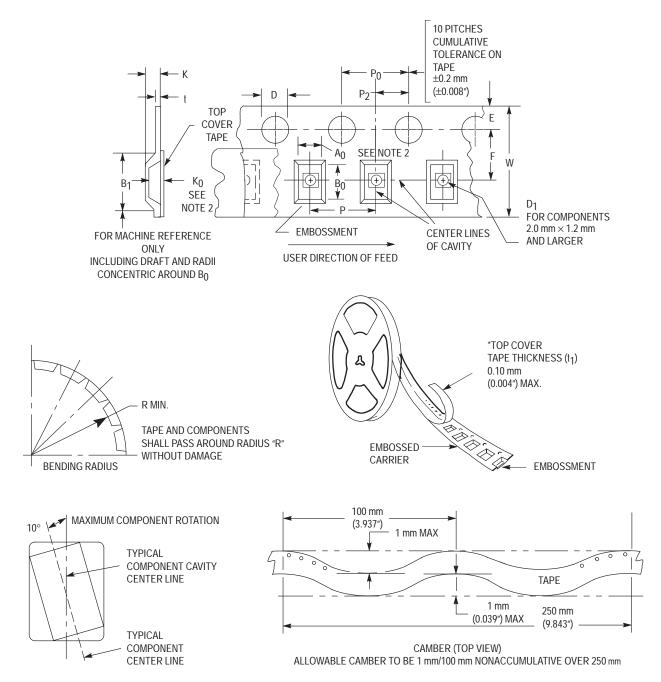


Figure 9. Carrier Tape Specifications

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

Tape Size	B ₁ Max	D	D ₁	E	F	К	Р	P ₀	P ₂	R	Т	w
24mm	20.1mm (0.791")	1.5 + 0.1mm -0.0 (0.059 +0.004" -0.0)	1.5mm Min (0.060")	1.75 ±0.1 mm (0.069 ±0.004")	11.5 ±0.10 mm (0.453 ±0.004")	11.9 mm Max (0.468")	16.0 ±0.1 mm (0.63 ±0.004")	4.0 ±0.1 mm (0.157 ±0.004")	2.0 ±0.1 mm (0.079 ±0.004")	30 mm (1.18")	0.6 mm (0.024")	24.3 mm (0.957")

- 1. Metric Dimensions Govern-English are in parentheses for reference only.
- 2. A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

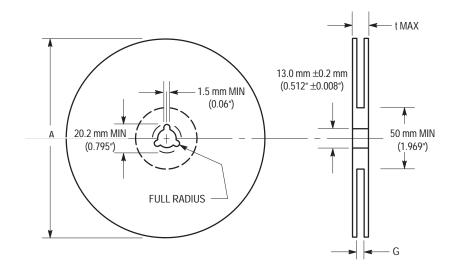


Figure 10. Reel Dimensions

REEL DIMENSIONS

Tape Size	A Max	G	t Max	
24 mm	360 mm	24.4 mm + 2.0 mm, -0.0	30.4 mm	
	(14.173")	(0.961" + 0.078", -0.00)	(1.197")	

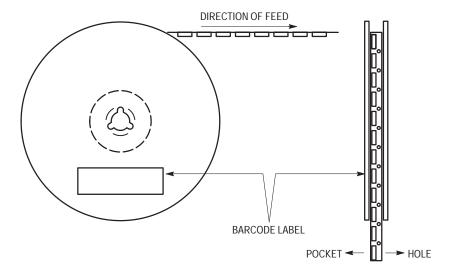


Figure 11. Reel Winding Direction

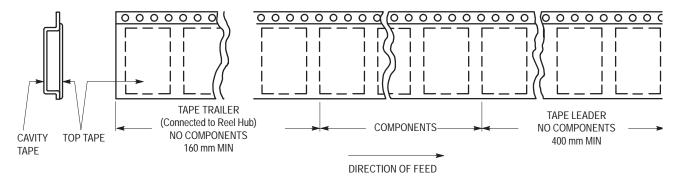


Figure 12. Tape Ends for Finished Goods

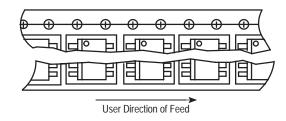


Figure 13. Reel Configuration

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